

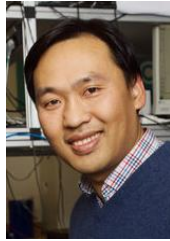


Electrical Characterization of Conductive Covalent- and Metal-Organic and Frameworks by Time Resolved THz Spectroscopy

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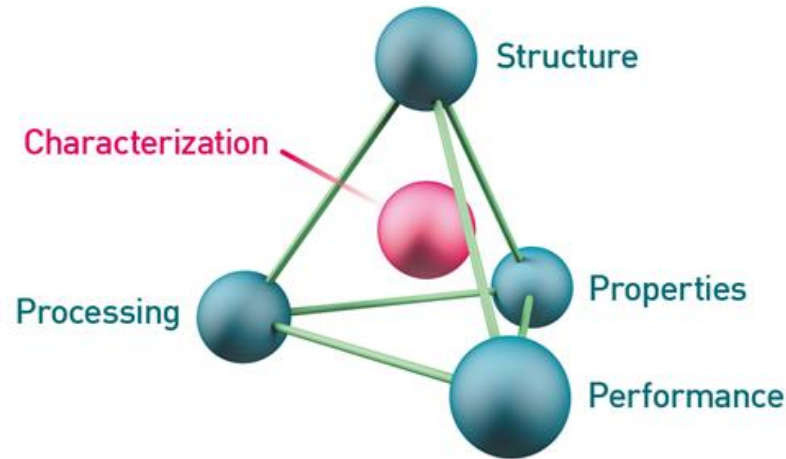


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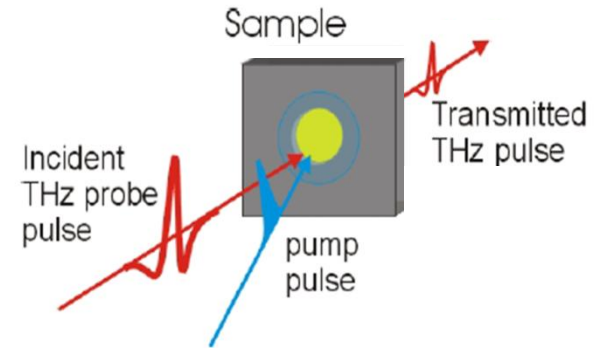


What we do?

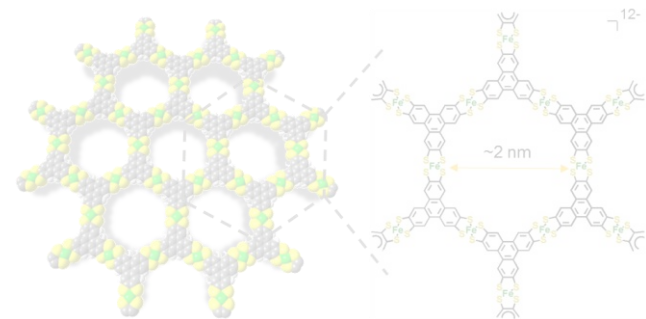


We aim establishing neat correlations between structure, processing, properties and functionality in **semiconductors and their hetero-structures**, with a focus on **carrier dynamics and charge transport**. Our main tool is **time resolved THz spectroscopy**.

time-resolved terahertz spectroscopy



Charge transport in metal- and covalent-organic frameworks



*Time resolved THz Spectroscopy:
a non-contact electrical probe at the
nanoscale with sub-ps resolution*

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Frequency

$$f = 1 \text{ THz} = 10^{12} \text{ Hz}$$

Oscillation period

$$T = 1/f = 1 \text{ ps}$$

Wavelength

$$cT = \lambda = 300 \text{ } \mu\text{m}$$

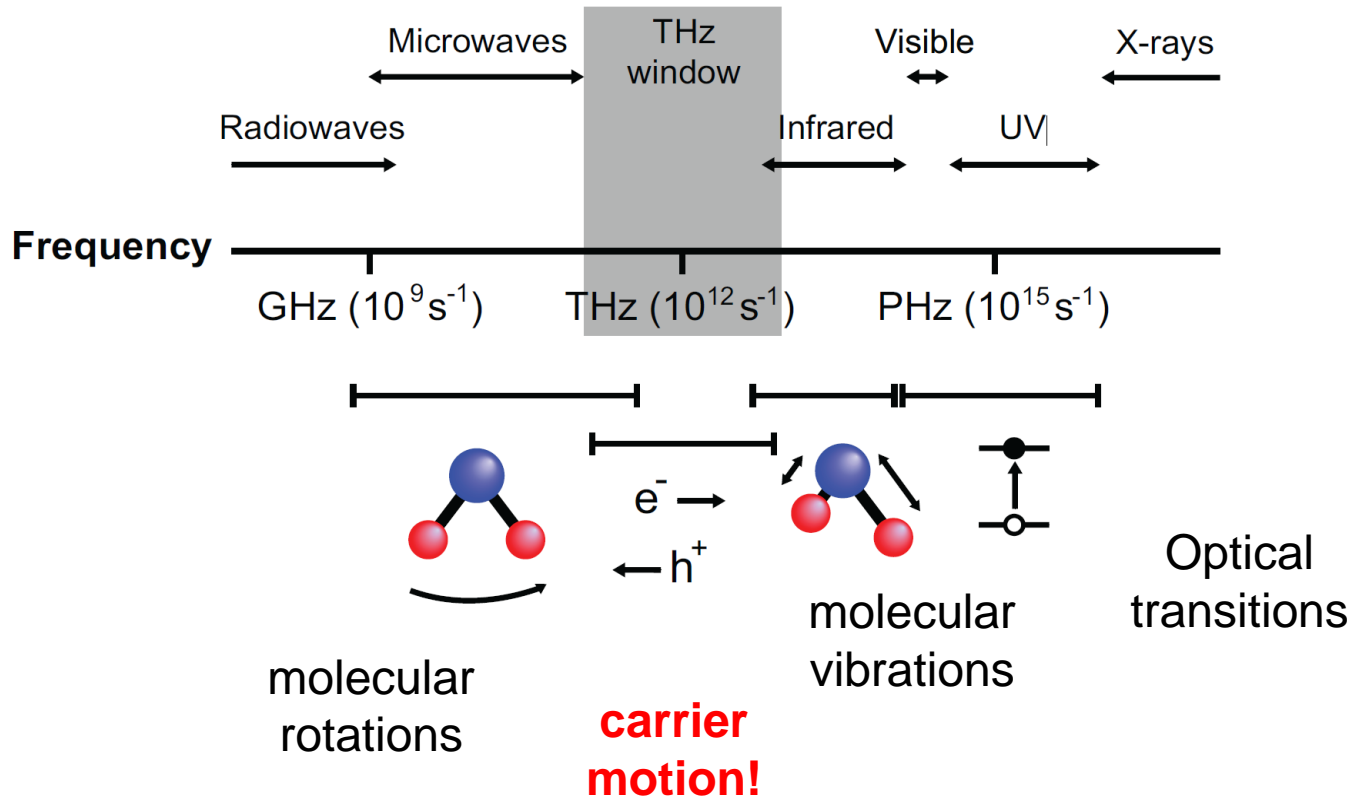
Wavenumbers

$$1/\lambda = 33 \text{ cm}^{-1}$$

Photon energy

$$h\omega = 4 \text{ meV}$$

Terahertz (THz) frequencies



we can measure carrier motion (conductivity) with THz light!

But... why and how?

Why THz radiation allows measuring carrier motion?

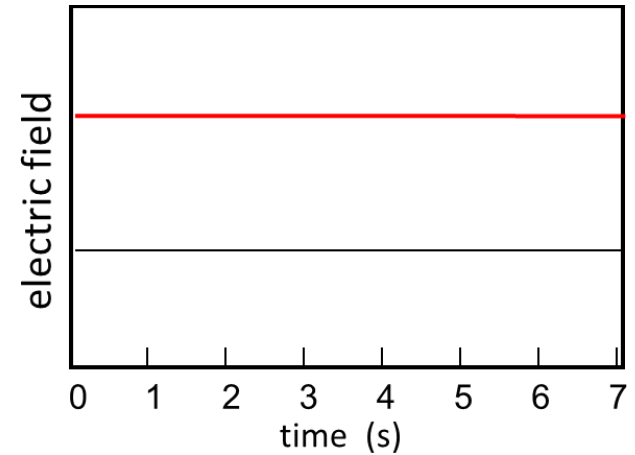


E. Muybridge, "The horse in motion" (1878).

To "capture" horse motion:
1 photo per milisecond ($10^{-3}s$).

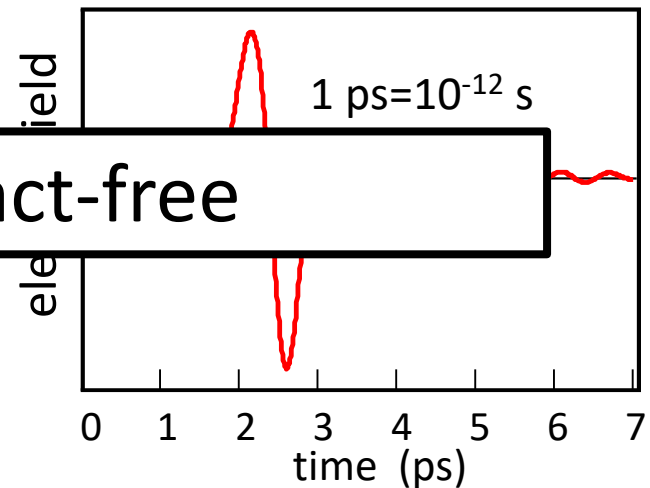
How do we measure conductivity by THz radiation?

Instead of this:

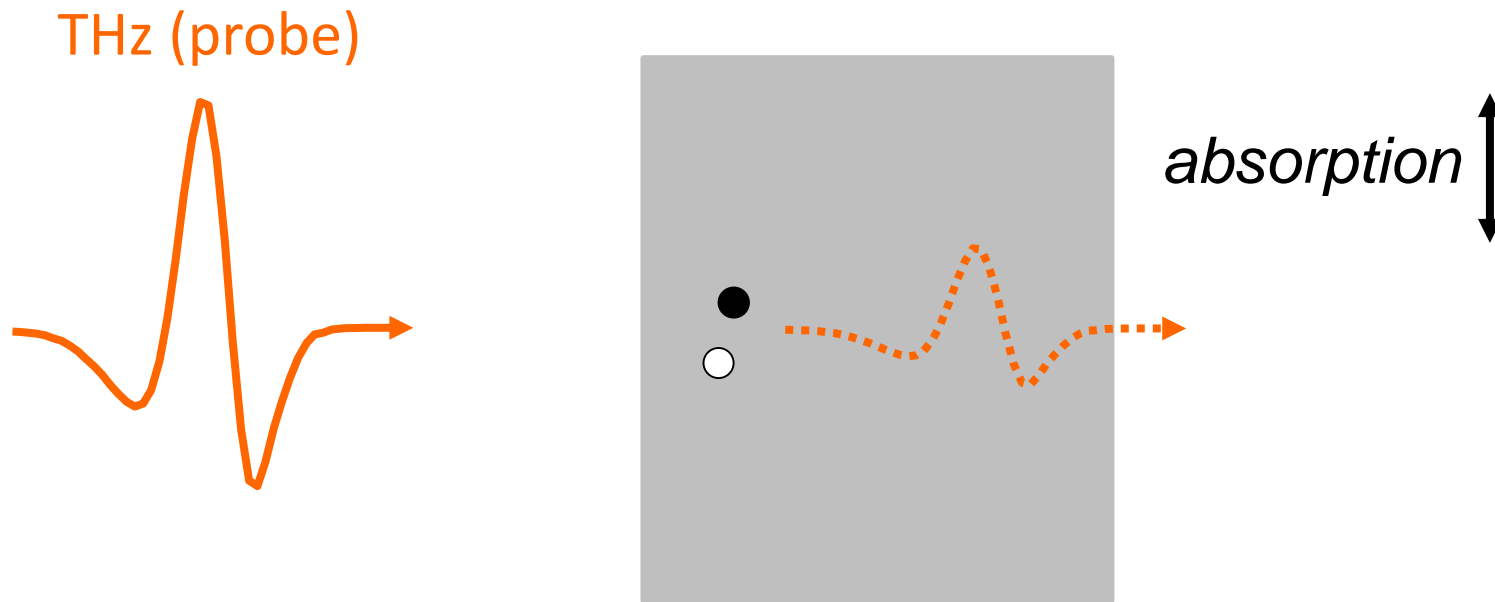


use

Ultrafast & contact-free



Terahertz (THz) spectroscopy

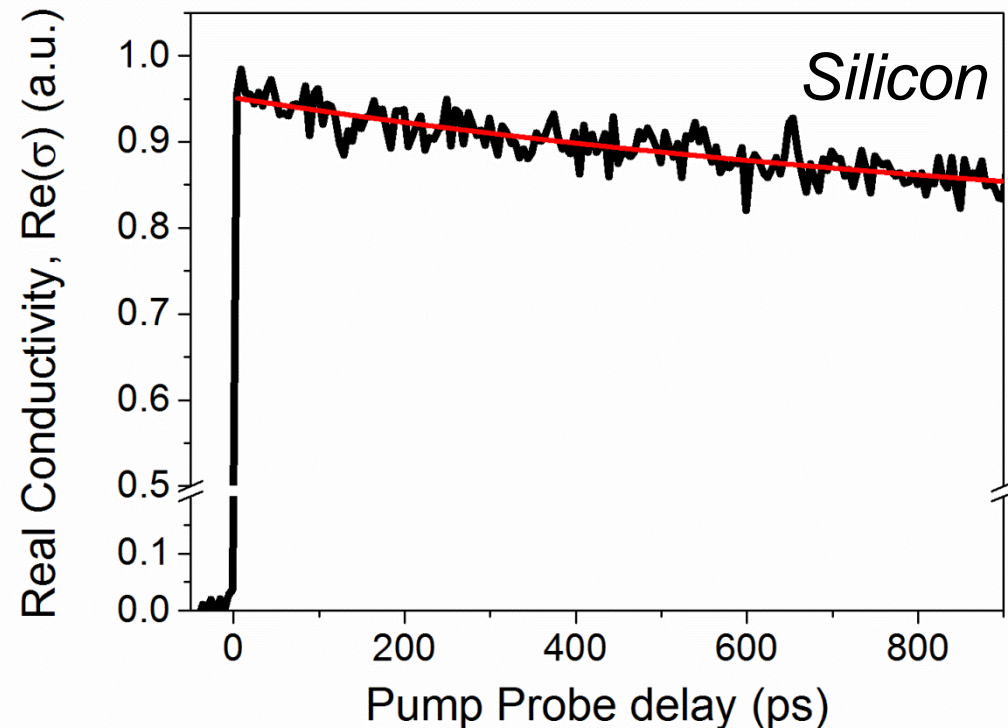


$$\text{Absorption} \sim \text{Re}(\sigma) = e \cdot N \cdot \mu$$

N = number of carriers

μ = sample's mobility

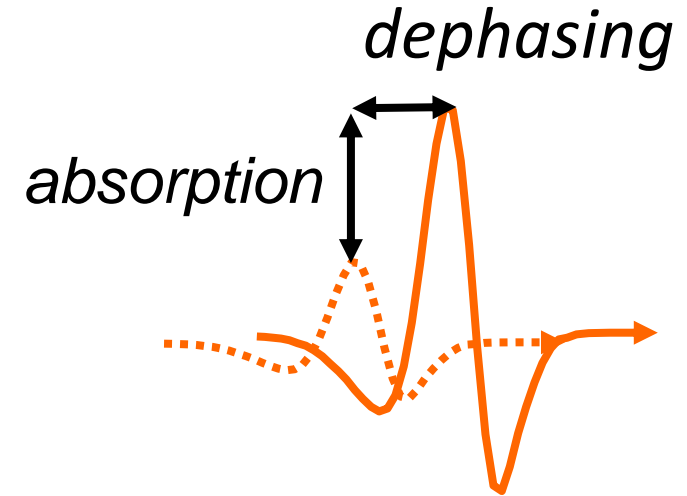
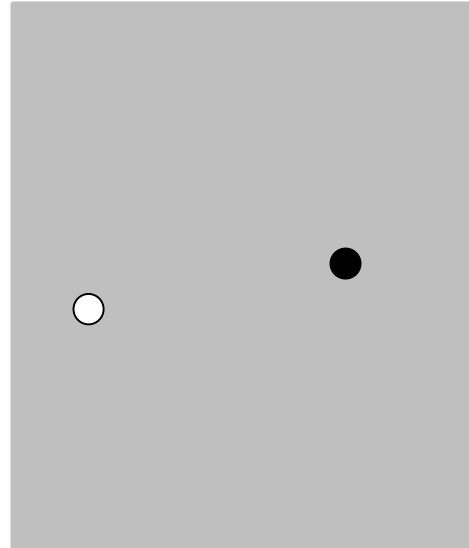
Absorption vs time after excitation $\sim \text{Re}[\sigma](t) = e \cdot N(t) \cdot \mu$



$$N(t) = N_{h\nu} \cdot \exp(-k \cdot t)$$

$N_{h\nu} \sim$ number photons

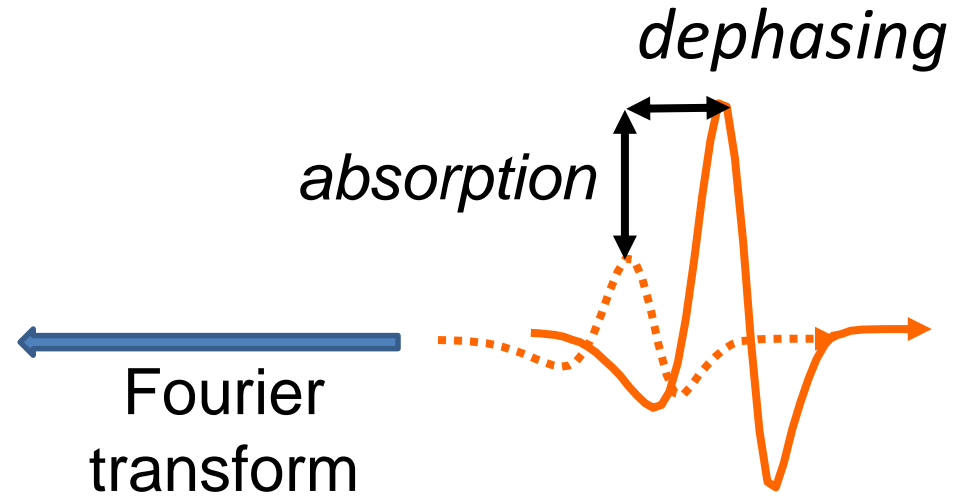
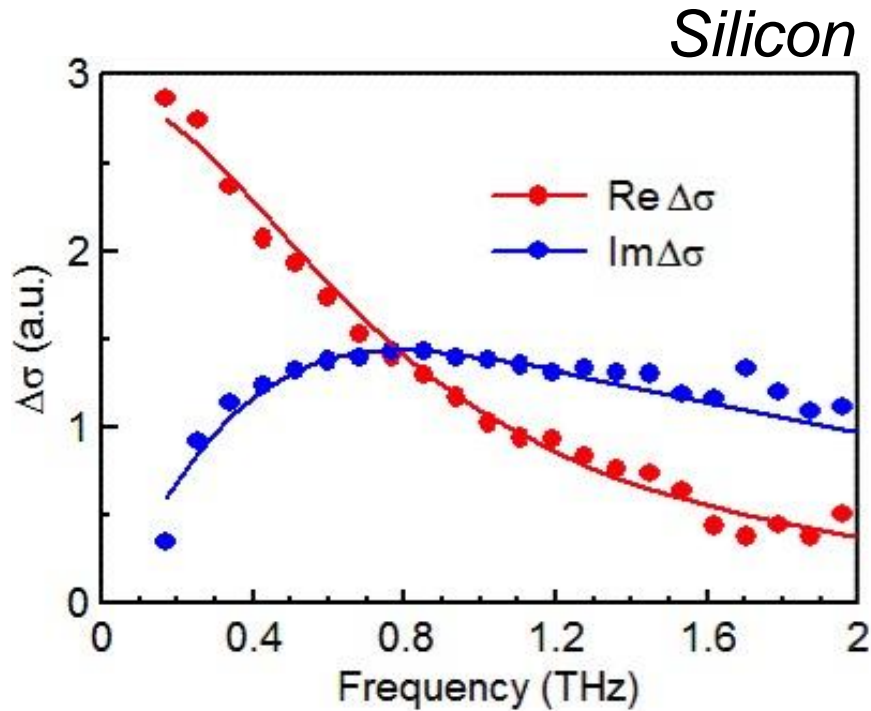
$k \sim$ rate constant



$$\text{Absorption} \sim \text{Re}(\sigma) = e \cdot N \cdot \mu$$

$$\text{Dephasing} \sim \text{Im}(\sigma)$$

Interrogating the nature of charge carriers

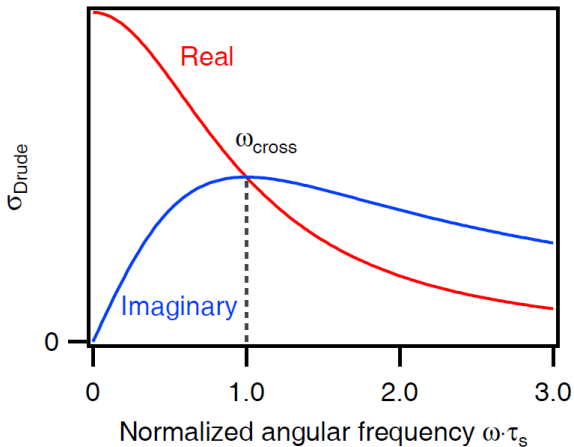


$$\text{Conductivity} \sim \sigma(\omega) = e \cdot N(t_0) \cdot \mu(\omega)$$

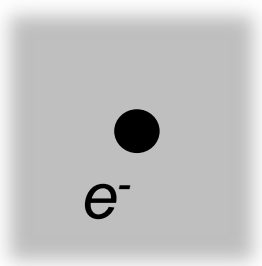
$\mu(\omega)$ is the frequency resolved mobility in the sample and is informative of the nature of the carriers!

Conductivity for free carriers (the Drude Model)

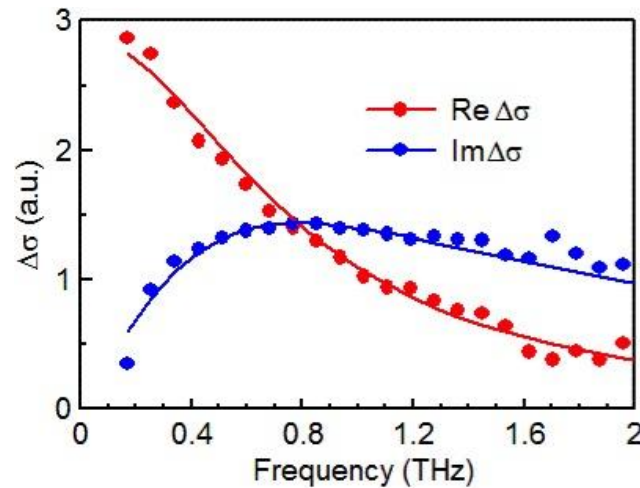
Drude Model



free carriers



Silicon



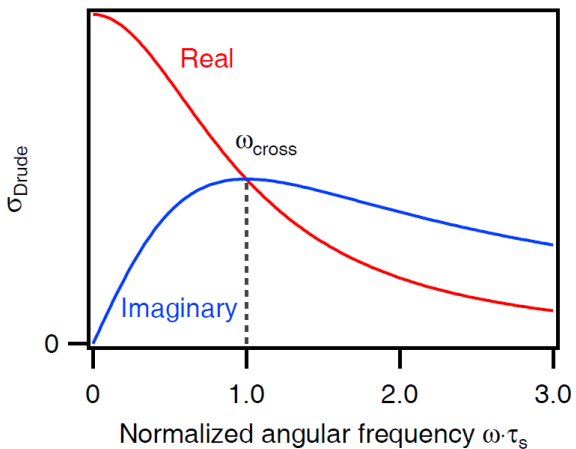
$$\sigma(\omega) = \frac{i\varepsilon_0\omega_p^2}{\omega + i\gamma} \quad \gamma = \frac{1}{\tau} \quad \omega_p^2 = \frac{Ne^2}{\varepsilon_0 m}$$

Scattering time, $\tau \rightarrow \mu(\omega)$

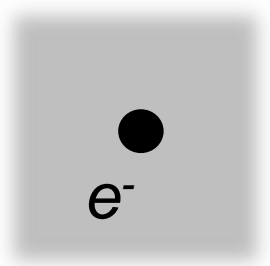
Plasma frequency $\omega_p^2 \rightarrow N$

Conductivity Models for Free Carriers and Excitons

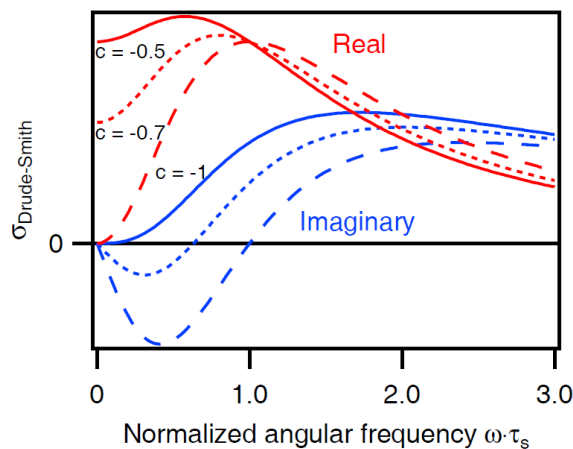
Drude Model



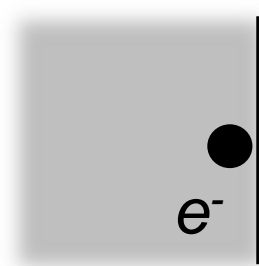
free carriers



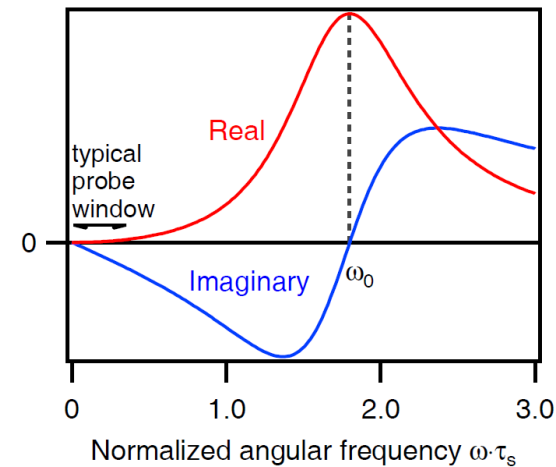
Drude-Smith Model



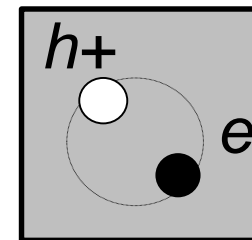
free carriers + backscattering



Lorentz Model



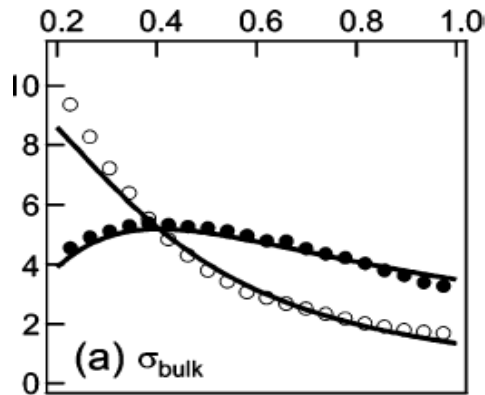
excitons



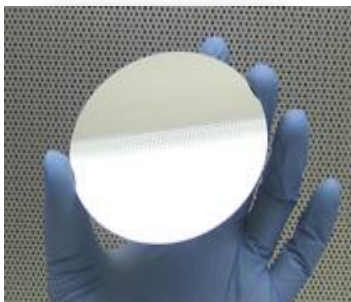
Increasing charge localization

Conductivity Models for Excitons and Free Carriers

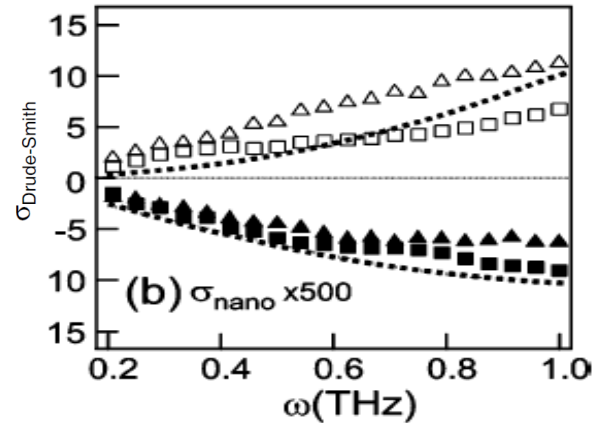
Drude Model



free carriers



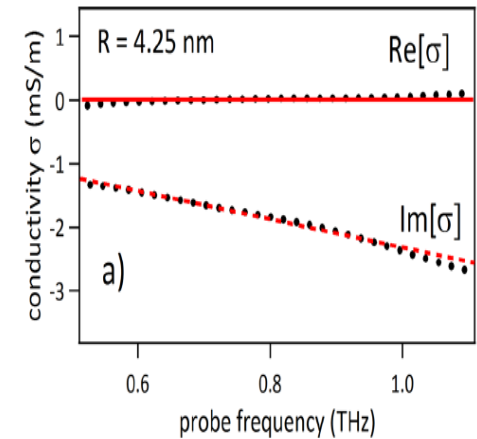
Drude-Smith Model



free carriers + backscattering



Lorentz Model



excitons



Increasing charge localization

- *THz spectroscopy allows for measuring sample's conductivity (ultrafast and contact free).*

$$\text{Conductivity} \sim \sigma(\omega) = e \cdot N \cdot \mu(\omega)$$

- *We can interrogate the fate of photo-generated carriers by monitoring the time evolution of carrier density, $N(t)$.*

$$N(t) = N_{h\nu} \cdot \exp(-k \cdot t) \quad \text{where } 1/k \text{ is carrier lifetime}$$

- *We can interrogate the nature of photo-generated carriers via modelling the frequency resolved conductivity (i.e. mobility).*

$$\text{Modelling } \mu(\omega) \rightarrow \text{carrier scattering time } \tau_r$$

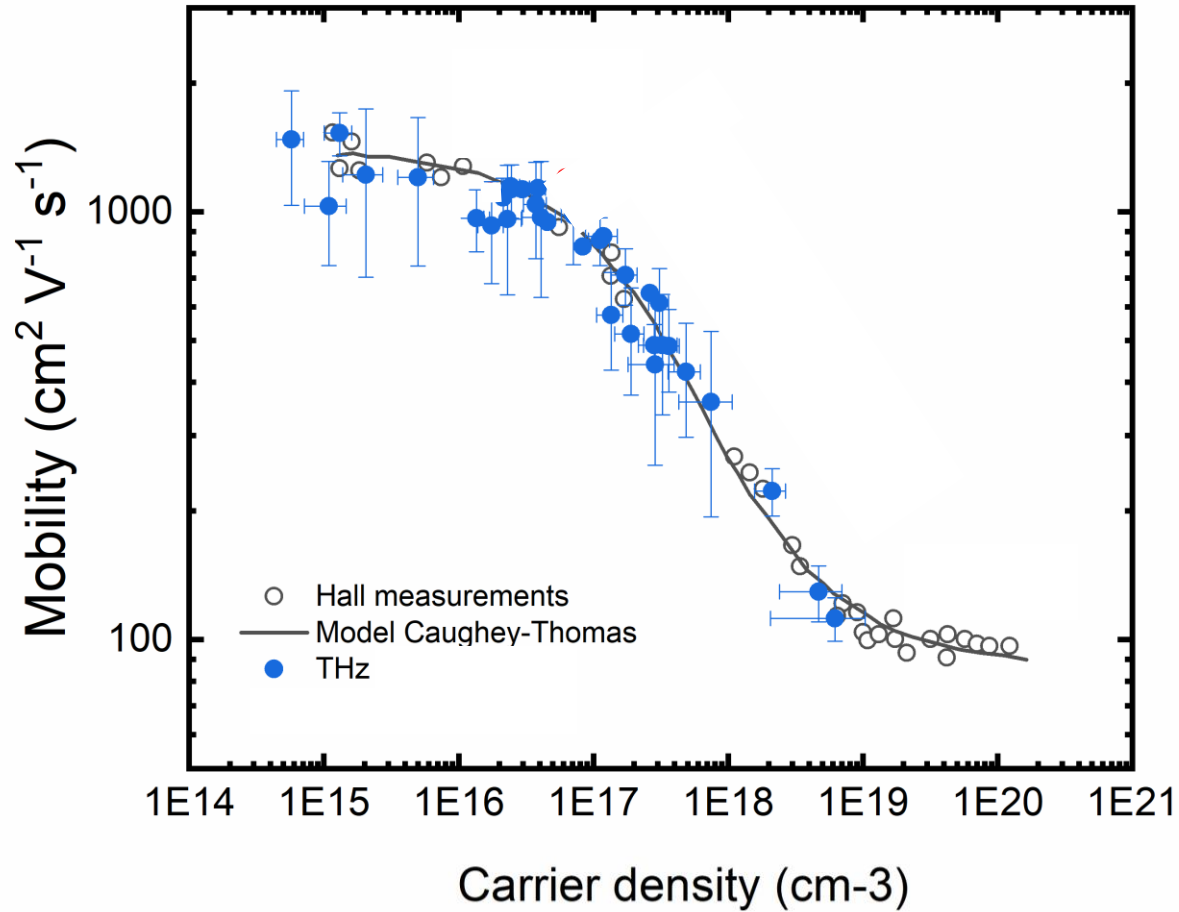
Piece of advice...

*“Theories come and go, but
good data remains forever”*



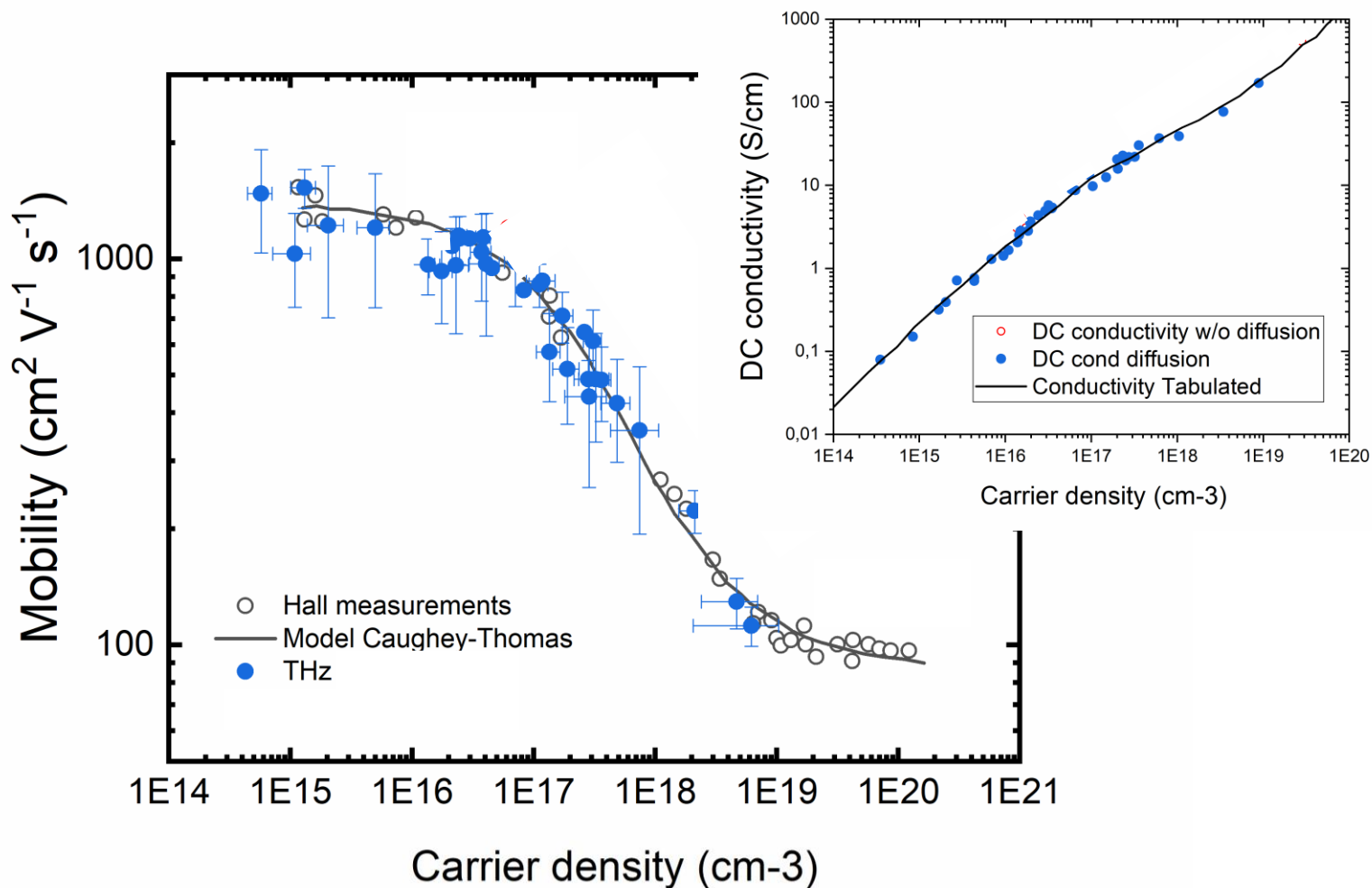
Mary Leakey

Optical vs electrical characterization on silicon wafers



Phys. Rev. B 107, 085204 (2023)

Optical vs electrical characterization on silicon wafers



Phys. Rev. B 107, 085204 (2023)

Piece of advice...

If it disagrees with experiment, it's wrong.

In that simple statement is the key to science.

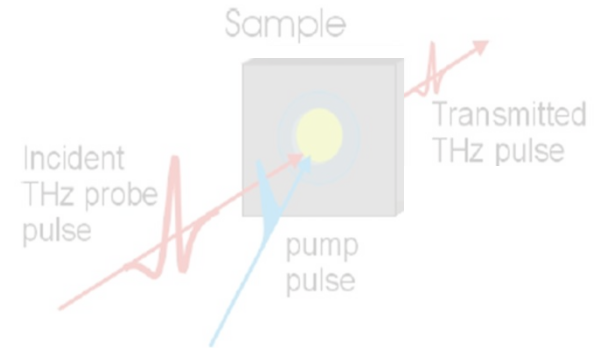
It doesn't make a difference how beautiful your guess is.

It doesn't matter how smart you are who made the guess, or what his name is;

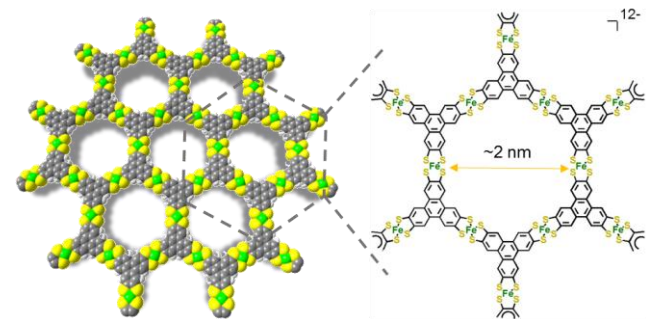
If it disagrees with experiment, it's wrong.

- Richard Feynman

time-resolved terahertz spectroscopy



Charge transport in metal- and covalent-organic frameworks



High-mobility band-like charge transport in a semiconducting 2D metal-organic framework

Renhao Dong^{1,#}, Peng Han^{2,#}, Himani Arora³, Marco Ballabio², Melike Karakus², Zhe Zhang¹, Chandra Shekhar⁴, Peter Adler⁴, Petko St. Petkov^{5,6}, Artur Erbe³, Stefan C. B. Mannsfeld¹, Claudia Felser⁴, Thomas Heine^{1,3,5}, Mischa Bonn², Xinliang Feng¹ and Enrique Cánovas^{2,7}

¹*Center for Advancing Electronics Dresden (cfaed) & Department of Chemistry and Food Chemistry, Technische Universität Dresden, Mommsenstrasse 4, 01062 Dresden, Germany*

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³*Helmholtz-Zentrum Dresden-Rossendorf & Center for Advancing Electronics Dresden (cfaed), 01328 Dresden, Germany*

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⁵*Wilhelm-Ostwald-Institute of Physical and Theoretical Chemistry, Leipzig University, Linnéstr. 2, 04103 Leipzig, Germany*

⁶*University of Sofia, Faculty of Chemistry and Pharmacy, J. Bourchier blvd. 1, 1164, Sofia, Bulgaria*

⁷*Instituto Madrileño de Estudios Avanzados en Nanociencia (IMDEA Nanociencia), Faraday 9, 28049 Madrid, Spain.*

Nature Materials 2018



Cubic Space Division
E. Mercuri (1954)



MOF-5
Yaghi (1999)

**MOFs are
generally
insulating 😞!**

Metal ions (or clusters) coordinated by organic ligands to form 1D, 2D and 3D crystalline materials:

- Countless combinations of building units (>100000 MOFs).
- Permanent crystalline porous structure (high surface area).
- Tunable functionality (gas storage and separation; catalysts and sensors; biomedical;...). **opto-electronics?,...)**

Development of Conductive Metal Organic Frameworks

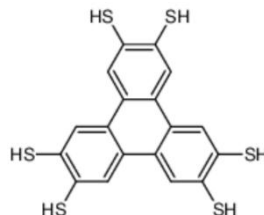
Target: High Conductivity!

$$\sigma = q \cdot N \cdot \mu$$

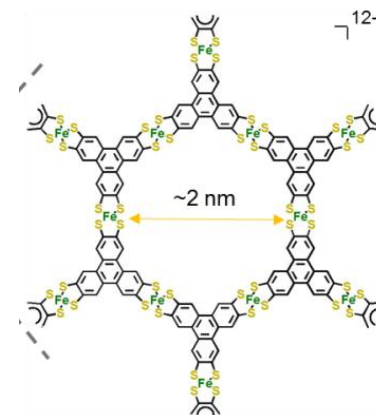
Enable high charge carrier densities via doping from metal ions (e.g. d^6 $\text{Fe}^{\text{II/III}}$) and/or organic ligands (e.g. radicals)

Enable high charge carrier mobilities via strong overlap between MOF building blocks orbitals.

Develop an iron based fully π -d conjugated 2D MOF



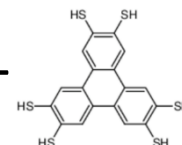
+ Fe(III) =



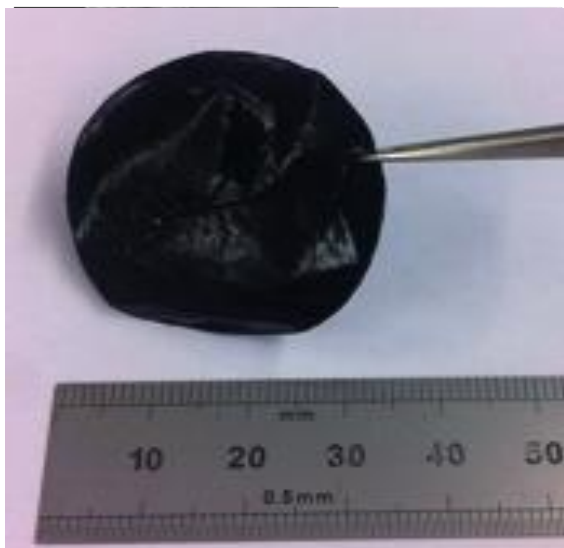


Water + $Fe(acac)_2$

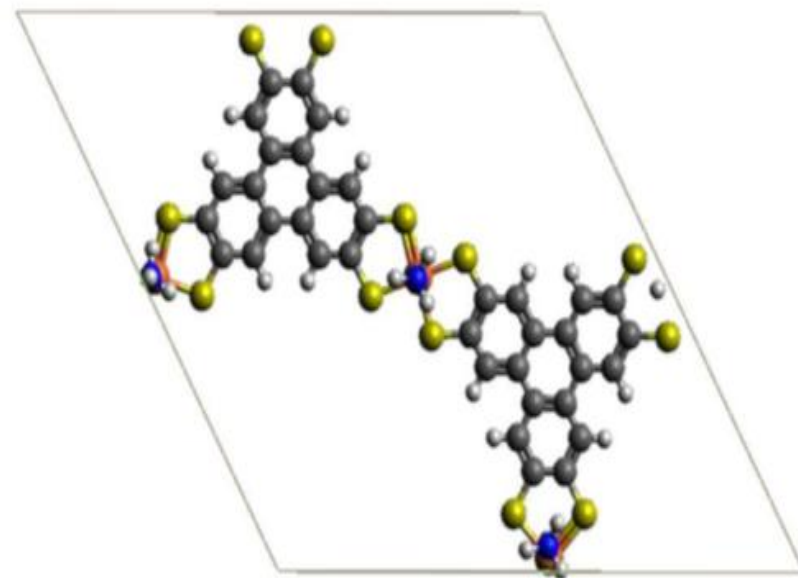
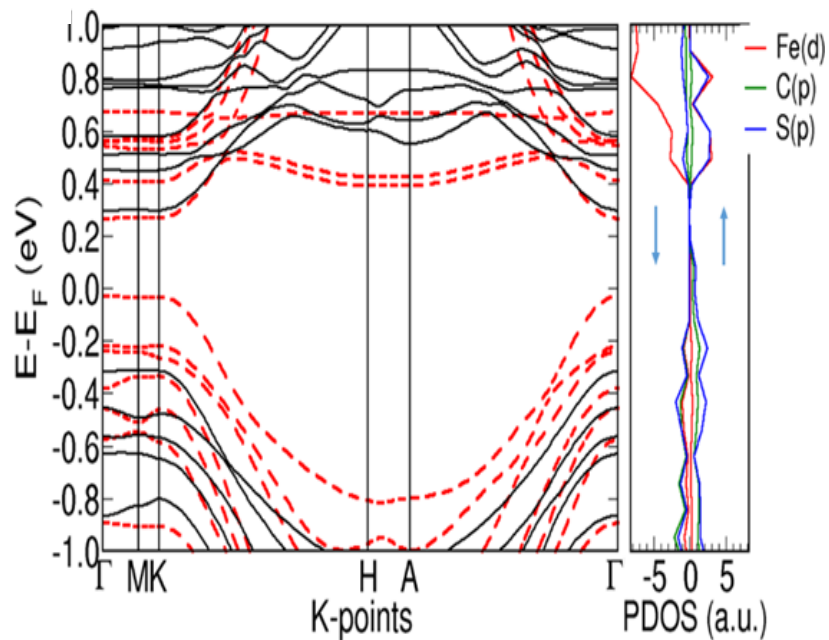
Chloroform +



Self-standing films

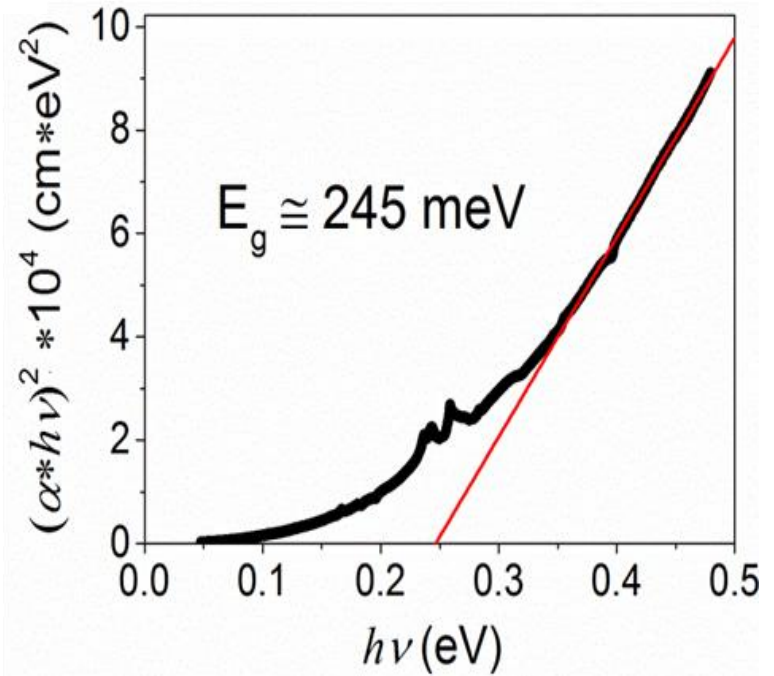
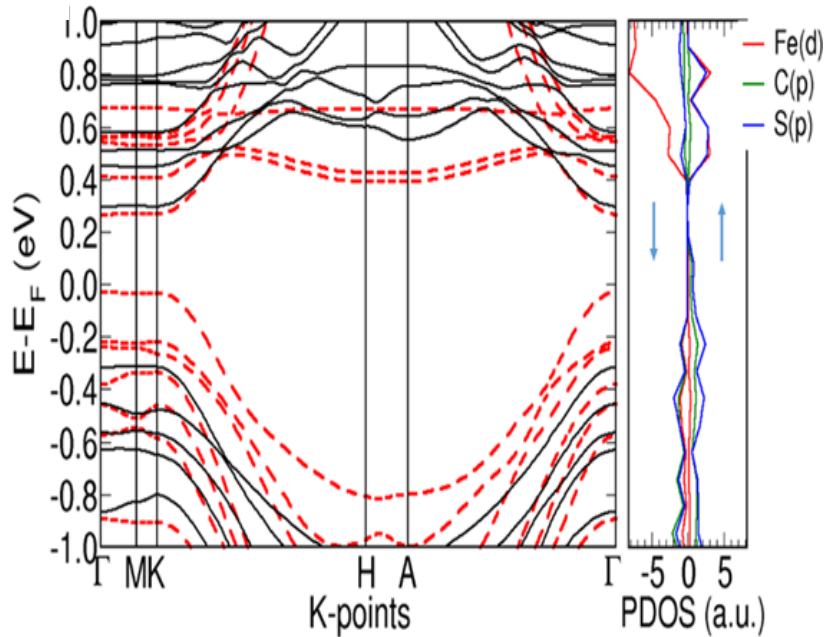


Semiconducting



Strong hybridization between metal and organic building blocks

Semiconducting



0.25eV direct bandgap

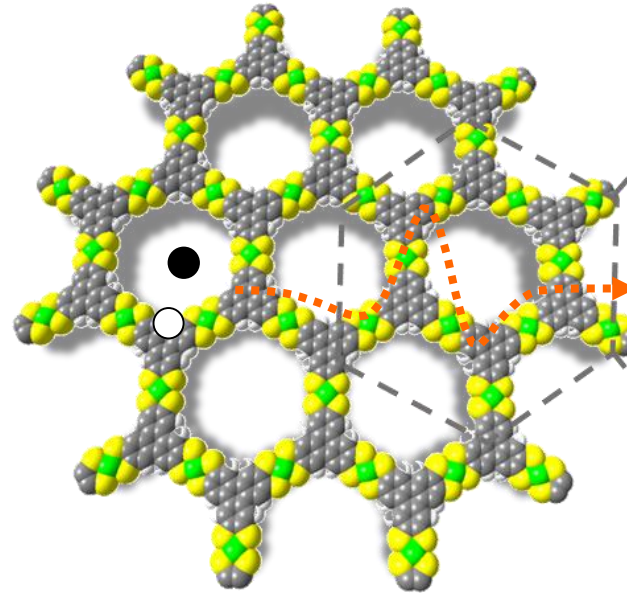
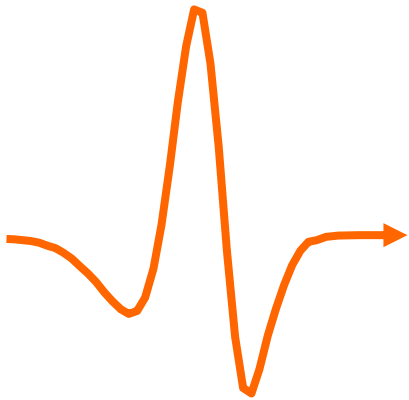


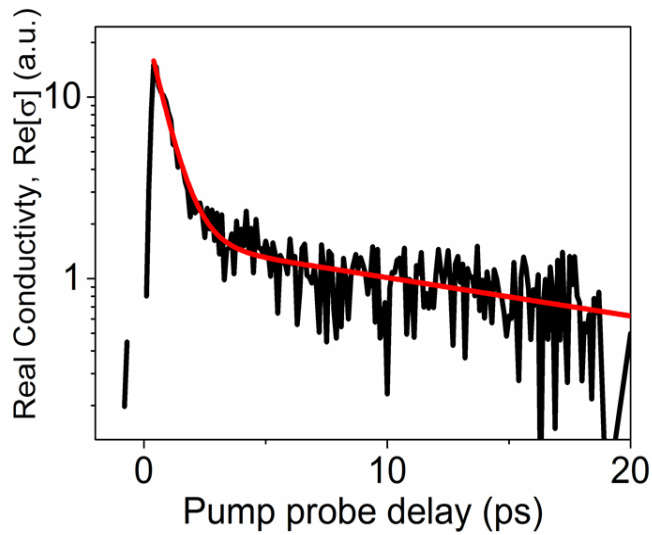
Time resolved THz spectroscopy

*Quantify photoconductivity
with ps time-resolution*

Contact free technique

THz (probe)





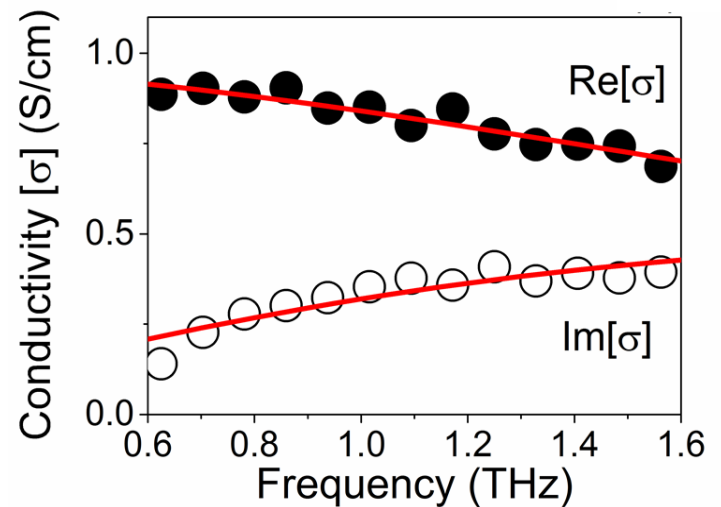
Fast photoconductivity relaxation

$$\text{Re}[\sigma](t) = q \cdot N(t) \cdot \mu$$

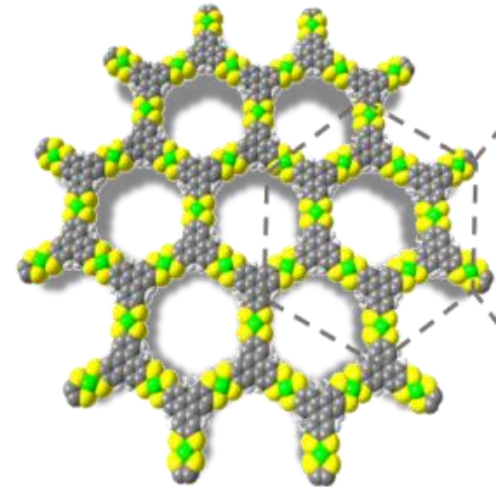
Drude response at the peak conductivity!

band-like transport in 2D MOFs!!!

$$\mu = 220 \text{ cm}^2/\text{Vs}$$



We resolve band like transport
in semiconducting 2D $\text{Fe}_3(\text{THT})_2$
MOF.

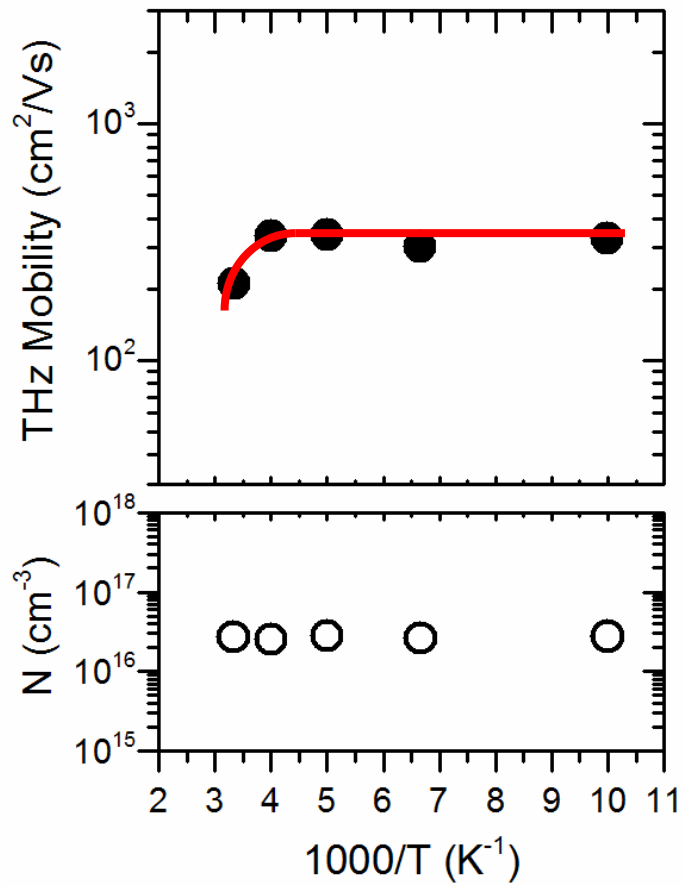


Can we improve the $220 \text{ cm}^2/\text{Vs}$ mobility?

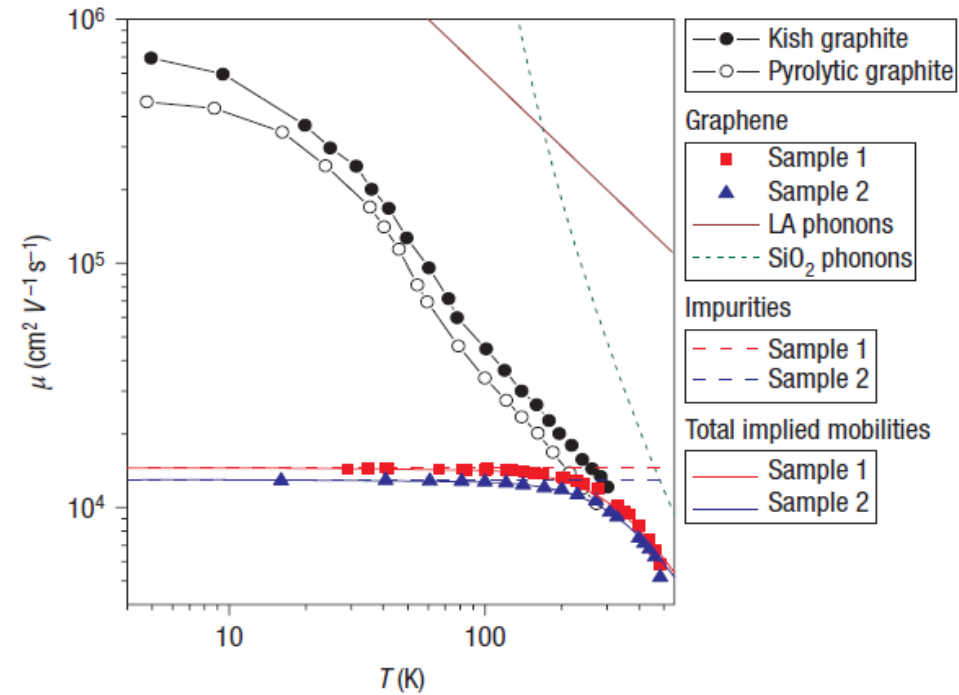
First identify scattering mechanisms limiting
mobility, how?

Analyze the temperature dependence.

2D MOF

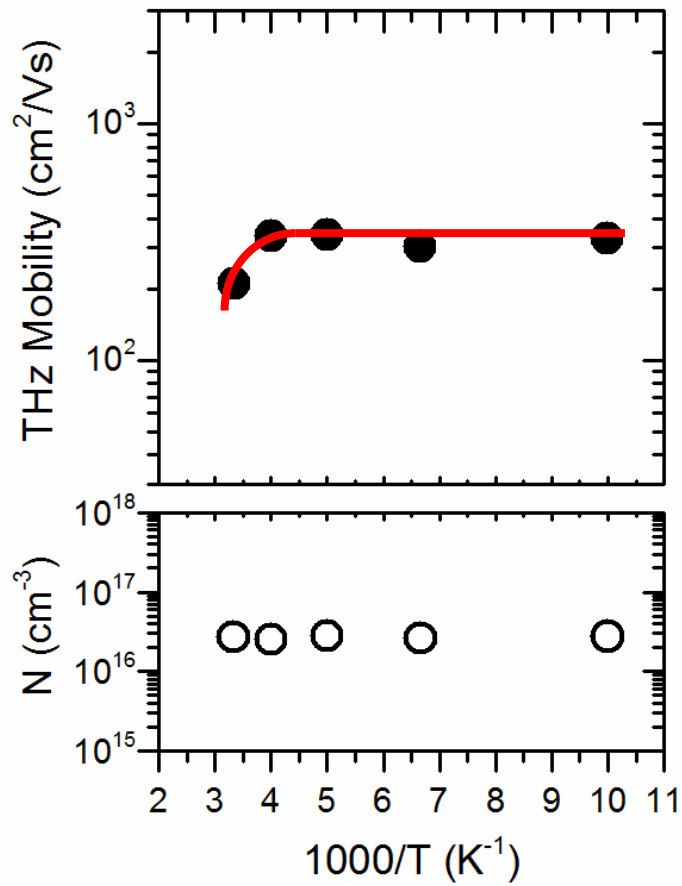


Graphene

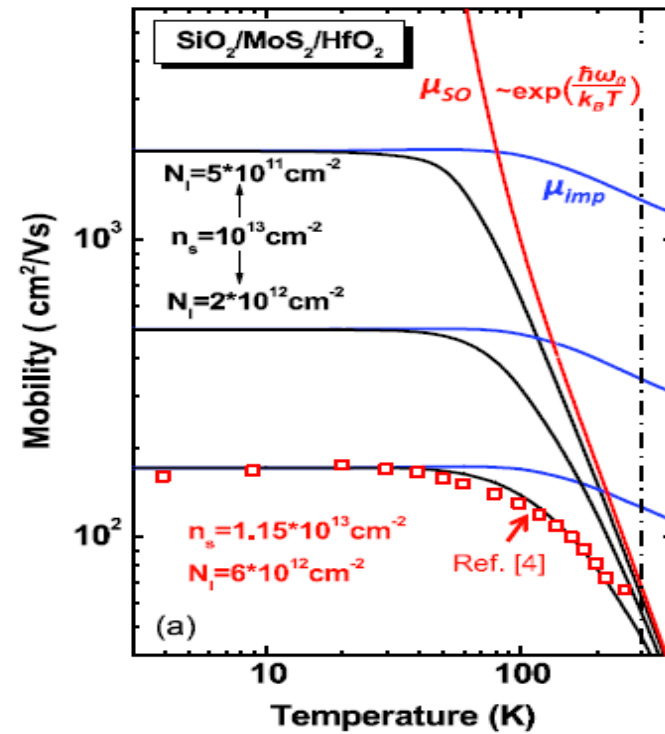


Nat. Nanotech. 3, 206 - 209 (2008)

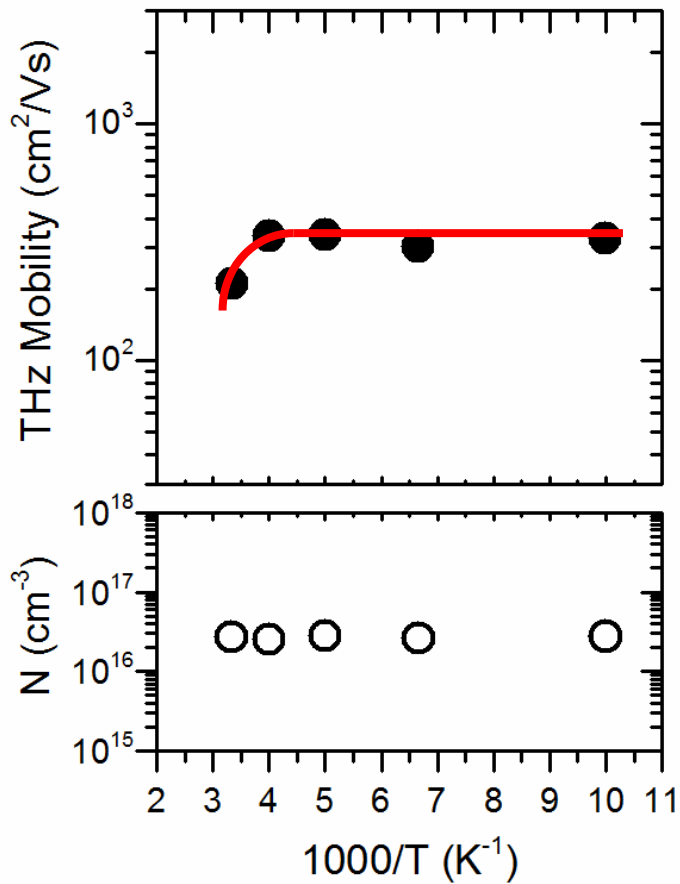
2D MOF



2D MoS₂



Phys. Rev. X 4, 011043 (2014)



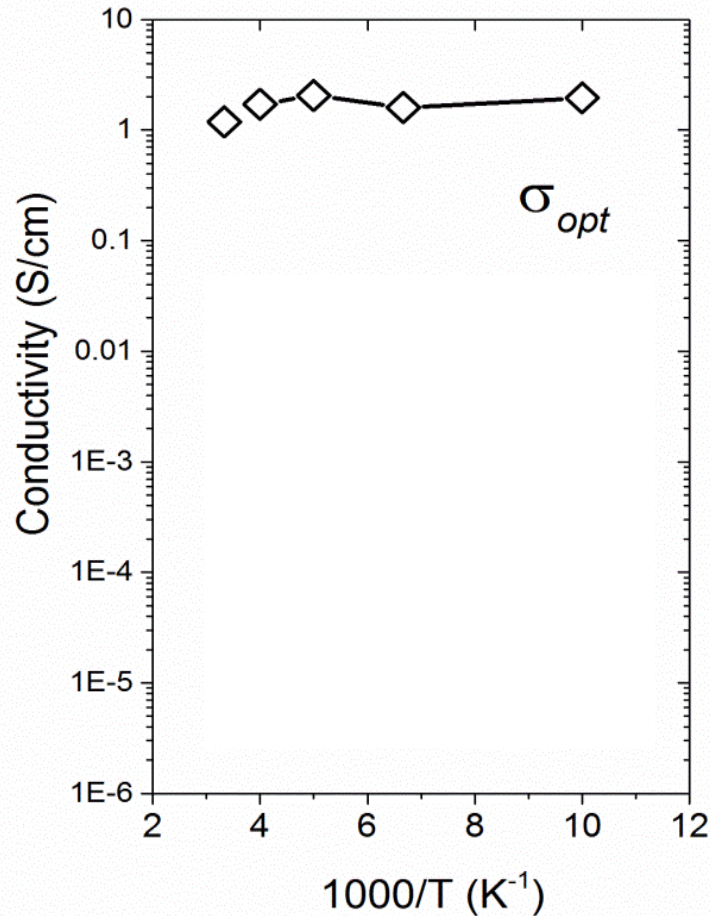
300-250K – phonon scattering.

>250K impurity scattering (heavy doping).

Doping engineering could boost mobilities values.

Comparing conductivities inferred optically and electrically

$$\sigma(\omega) = e \cdot N \cdot \mu(\omega)$$



Optical σ probed locally (nm's)

Mobility constant with T.

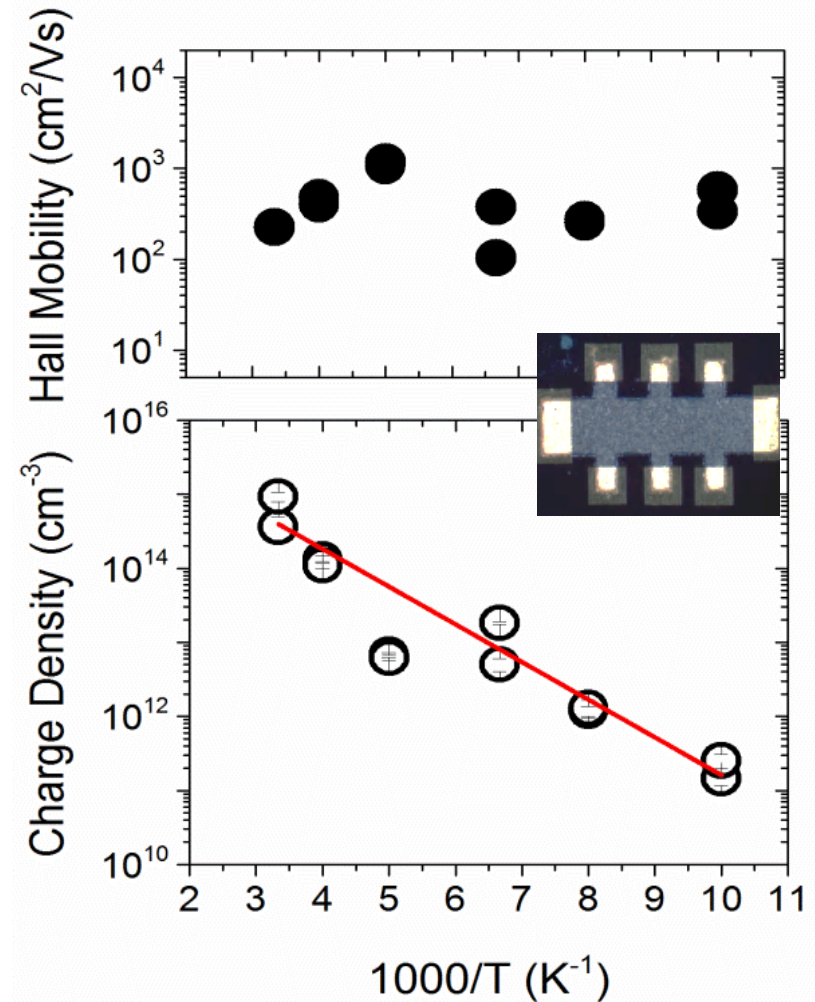
Carrier density fixed by #photons.

Hall Effect Measurements on 2D MOF

Hall (DC) mobility barely affected by temperature.

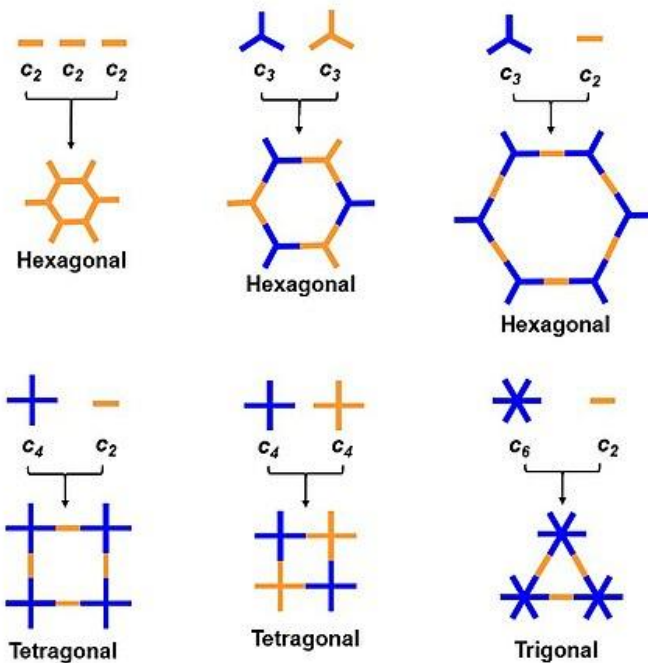
Temperature dependence of the electrical σ is dominated by intrinsic thermal population of carriers.

$$N_i \propto \exp(-E_g/2k_bT); E_g = 250\text{meV}$$



- *High-mobility band-like transport demonstrated in a semiconducting 2D metal organic framework (opened the path for MOF based opto-electronics).*
- *2D $Fe_3(THT)_2$ MOF samples display room temperature mobilities up to $220\text{cm}^2/\text{Vs}$. Further improvements in mobilities are possible via doping and phonon engineering.*

What about covalent organic frameworks?



Exceptionally high charge mobility in phthalocyanine-based poly(benzimidazobenzophenanthroline)-ladder-type two-dimensional conjugated polymers

Mingchao Wang^{1,10}, Shuai Fu^{2,10}, Petko St. Petkov³, Yubin Fu^{1,4}, Zhitao Zhang⁵, Yannan Liu^{1,4}, Ji Ma^{1,4}, Guangbo Chen¹, Sai Manoj Gali⁶, Lei Gao², Yang Lu^{1,4}, Silvia Paasch¹, Haixia Zhong¹, Hans-Peter Steinrück⁷, Enrique Cánovas^{2,8}, Eike Brunner¹, David Beljonne⁶, Mischa Bonn², Hai I. Wang^{2*}, Renhao Dong^{1,9*}, Xinliang Feng^{1,4*}

¹Center for Advancing Electronics Dresden (cfaed) & Faculty of Chemistry and Food Chemistry, Technische Universität Dresden, Mommsenstrasse 4, 01062 Dresden, Germany

²Max Planck Institute for Polymer Research, Ackermannweg 10, 55128 Mainz, Germany

³Faculty of Chemistry and Pharmacy, University of Sofia, 1164 Sofia, Bulgaria

⁴Max Planck Institute of Microstructure Physics, Weinberg 2, 06120 Halle, Germany

⁵Anhui Province Key Laboratory of Condensed Matter Physics at Extreme Conditions, High Magnetic Field Laboratory, HFIPS, Chinese Academy of Sciences, Hefei 230031, China

⁶Laboratory for Chemistry of Novel Materials, University of Mons, Place du Parc 20, 7000 Mons, Belgium

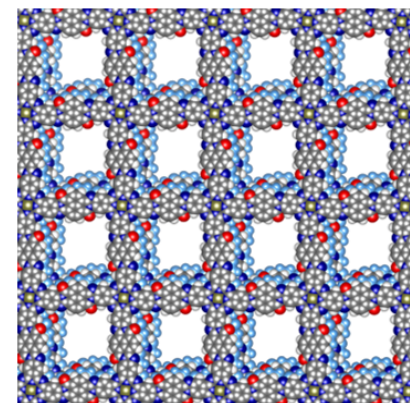
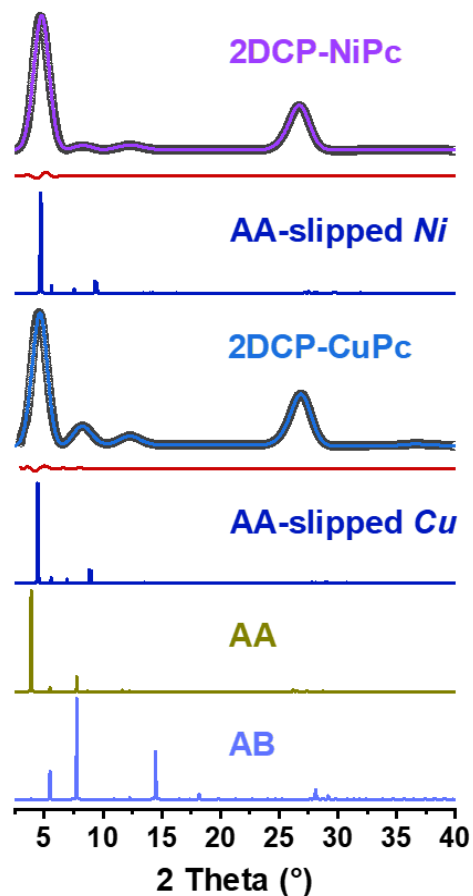
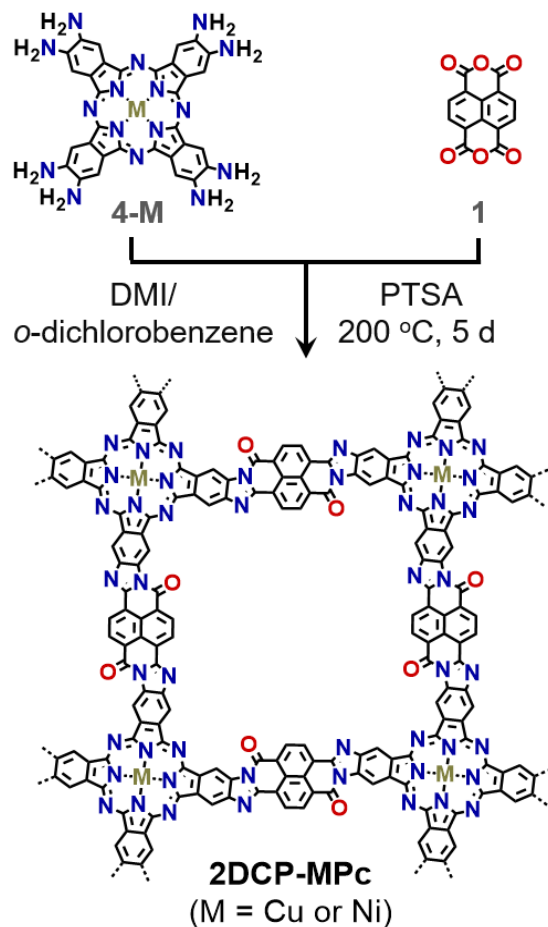
⁷Institute of Physical Chemistry II, Friedrich-Alexander-Universität Erlangen-Nürnberg, Egerlandstr. 3, 91058 Erlangen, Germany

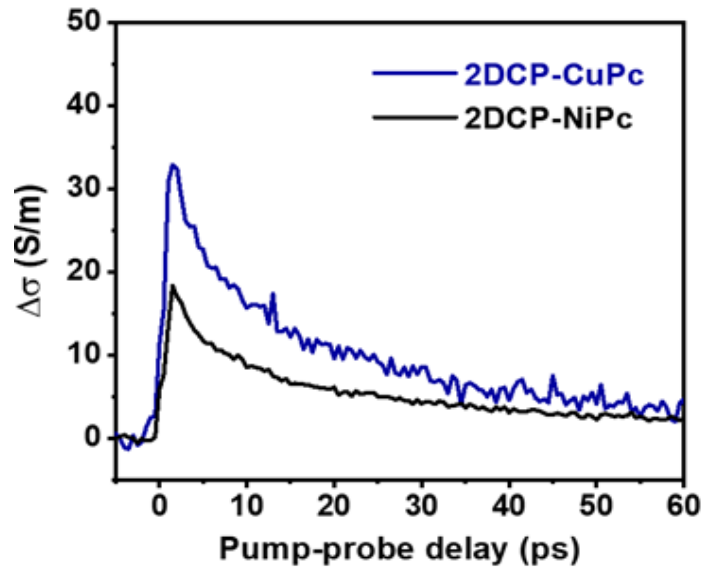
⁸Instituto Madrileño de Estudios Avanzados en Nanociencia (IMDEA Nanociencia), Faraday 9, 28049 Madrid, Spain.

⁹Key Laboratory of Colloid and Interface Chemistry of the Ministry of Education, School of Chemistry and Chemical Engineering, Shandong University, 250100 Jinan, China

Nature Materials 2023

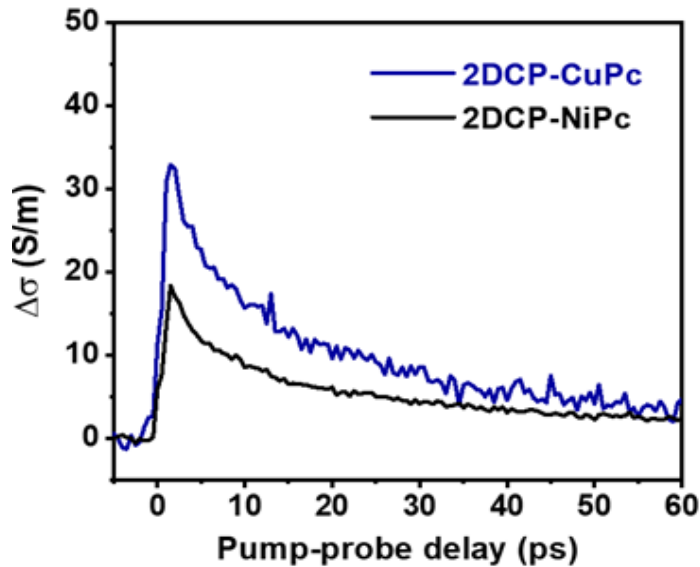
Phthalocyanine-based BBL-ladder-type COFs





*Fast photoconductivity
relaxation*

$$\text{Re}(\sigma) = q \cdot (n \cdot \mu)$$

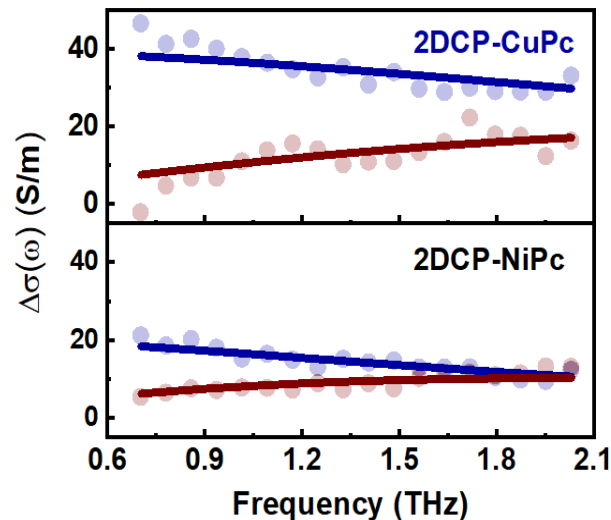


Fast photoconductivity relaxation

$$\text{Re}(\sigma) = q \cdot (n \cdot \mu)$$

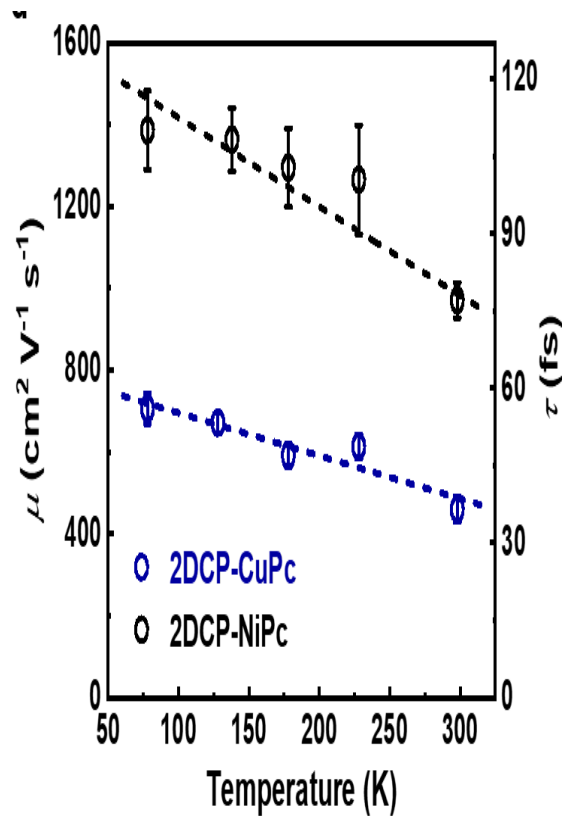
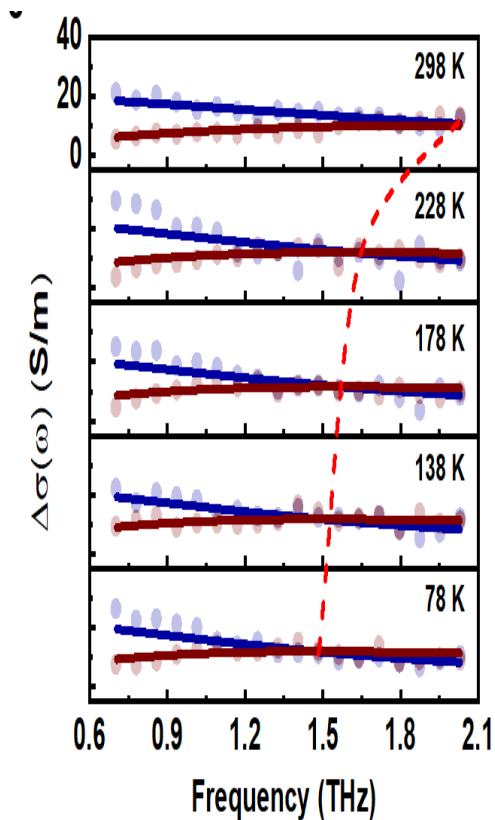
Drude responses at the peak conductivity!

High-mobility band-like transport in 2D COFs!



$$\mu = 460 \text{ cm}^2/\text{Vs}$$

$$\mu = 970 \text{ cm}^2/\text{Vs}$$



300-250K – phonon scattering.
 >250K impurity scattering (heavy doping).

Doping engineering could boost mobilities values.

- *High-mobility band-like transport demonstrated in semiconducting 2D covalent organic frameworks.*
- *Analyzed 2D-COF samples display bandgaps of 1.3eV and world record room temperature mobilities up to 970cm²/Vs (figures commensurate with Silicon but adding porosity and chemical tailorability)*

2D MOF and 2D COF semiconducting samples provide record-high mobilities up to 220 and 970 cm²/Vs respectively.

These figures parallel those found in inorganic semiconductors, but on porous and highly tailorable materials.

Further improvements are possible by developing single crystalline samples and by defect engineering.

Piece of advice...

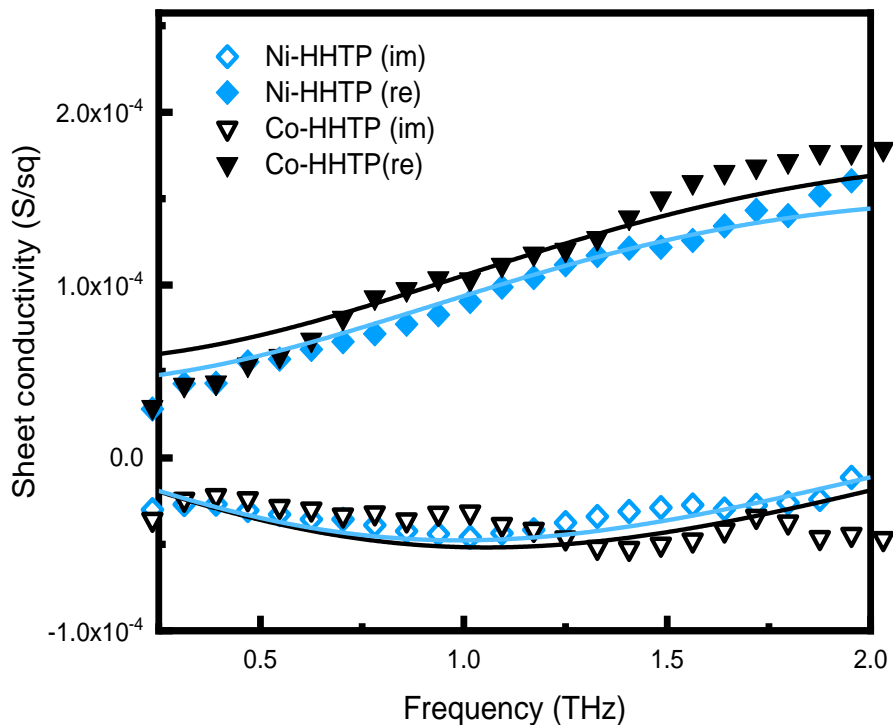
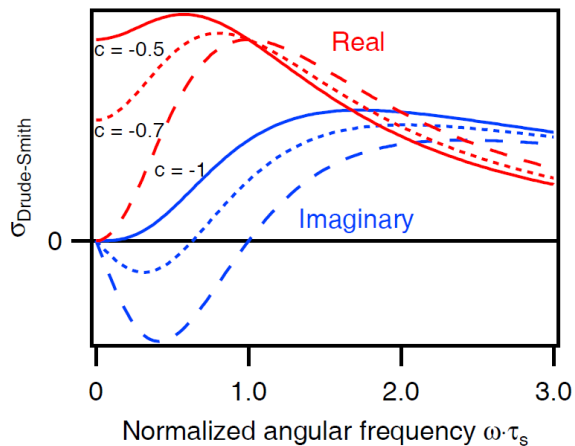
“The first principle is that you must not fool yourself—and you are the easiest person to fool.”

—Richard Feynman

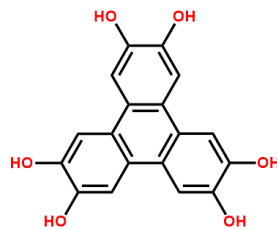
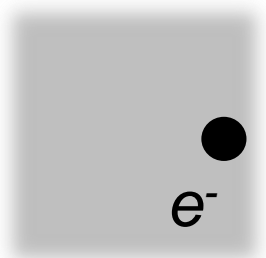


(Cu,Co)₃-HHTP₂

Drude-Smith Model



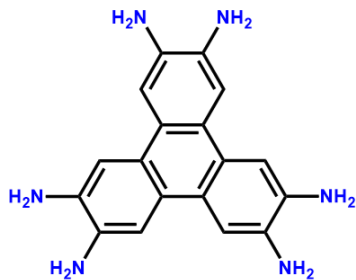
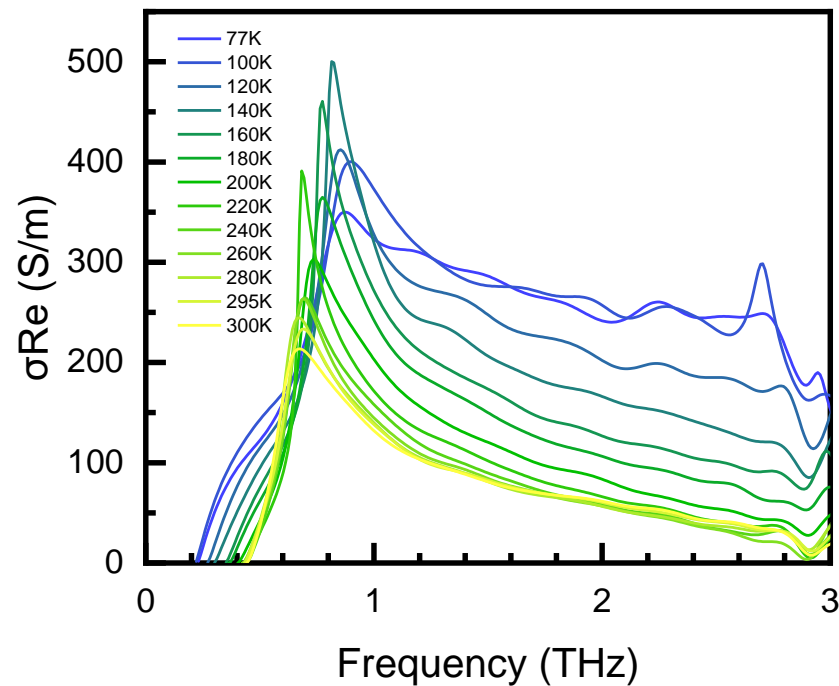
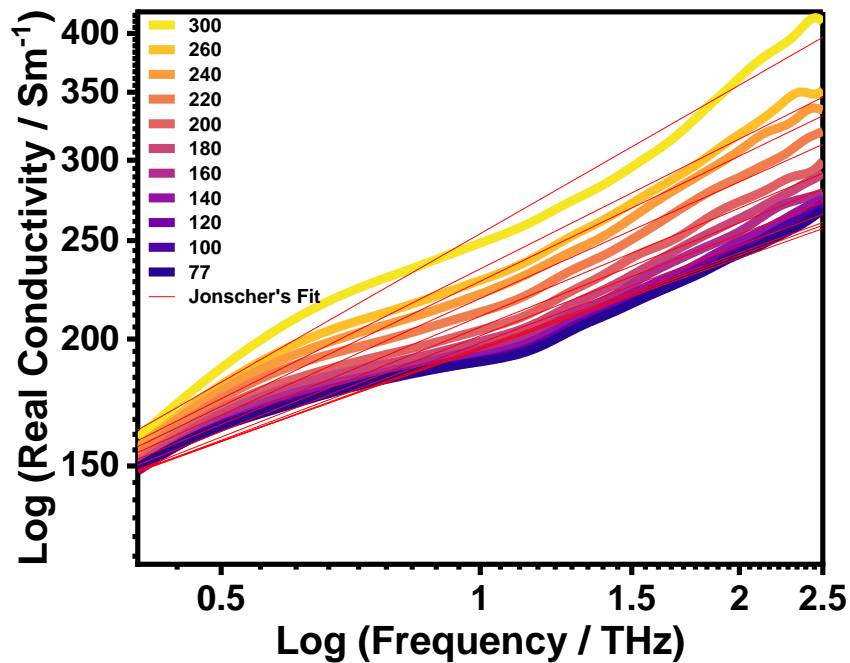
free carriers + backscattering



HHTP

Different metal center....
But same mobility,
“doping”, backscattering...

Ni₃-HITP₂



HITP

Same sample, different local “exotic” responses...

Nice, but... a lot to be done yet.

THE GOOD: Drude-like band-like transport high mobility/conductivity demonstrated for metallic and semiconducting samples.

THE BAD: sample reproducibility (even within same sample/group), degradation/oxidation, large single crystals not available....

THE UGLY: Library of materials expanding, sample's all surface, "doping" seems perturbative, little known about role of defects, short-lived charge carriers, DFT support limited to pristine samples....

